

# MOSFET - Power, Single N-Channel, D<sup>2</sup>PAK7

## 80 V, 1.34 mΩ, 290 A



ON Semiconductor®

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## NVBGS1D2N08H

### Features

- Low R<sub>DS(on)</sub> to Minimize Conduction Losses
- Low Q<sub>G</sub> and Capacitance to Minimize Driver Losses
- AEC-Q101 Qualification
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>	80	V
Gate-to-Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current R <sub>θJC</sub> (Note 2)	I <sub>D</sub>	T <sub>C</sub> = 25°C	290
		T <sub>C</sub> = 100°C	205
Power Dissipation R <sub>θJC</sub> (Note 2)	P <sub>D</sub>	T <sub>C</sub> = 25°C	259
		T <sub>C</sub> = 100°C	130
Continuous Drain Current R <sub>θJA</sub> (Notes 1, 2)	I <sub>D</sub>	T <sub>A</sub> = 25°C	43
		T <sub>A</sub> = 100°C	31
Power Dissipation R <sub>θJA</sub> (Notes 1, 2)	P <sub>D</sub>	T <sub>A</sub> = 25°C	5.7
		T <sub>A</sub> = 100°C	2.9
Pulsed Drain Current	T <sub>A</sub> = 25°C, t <sub>p</sub> = 100 μs	I <sub>DM</sub>	900
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C
Source Current (Body Diode)	I <sub>S</sub>	199	A
Single Pulse Drain-to-Source Avalanche Energy (I <sub>L</sub> = 32 A <sub>pk</sub> )	E <sub>AS</sub>	1500	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T <sub>L</sub>	260	°C

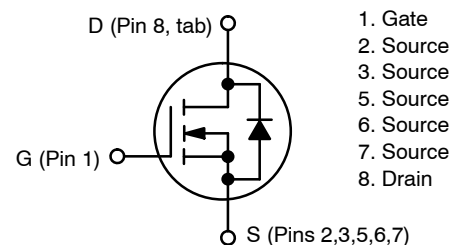
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL RESISTANCE MAXIMUM RATINGS

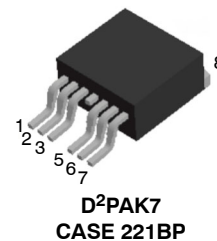
Parameter	Symbol	Value	Unit
Junction-to-Case - Steady State (Note 2)	R <sub>θJC</sub>	0.58	°C/W
Junction-to-Ambient - Steady State (Note 1)	R <sub>θJA</sub>	26.2	

1. Surface-mounted on FR4 board using a 1 in<sup>2</sup> pad size, 2 oz. Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

V <sub>(BR)DSS</sub>	R <sub>DS(ON) MAX</sub>	I <sub>D MAX</sub>
80 V	1.34 mΩ @ 10 V	290 A

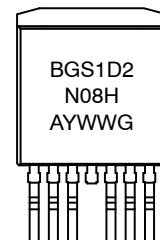


N-CHANNEL MOSFET



D<sup>2</sup>PAK7  
CASE 221BP

### MARKING DIAGRAM



BGS1D2N08H = Specific Device Code  
 A = Assembly Location  
 Y = Year  
 WW = Work Week  
 G = Pb-Free Package

### ORDERING INFORMATION

Device	Package	Shipping†
NVBGS1D2N08H	D <sup>2</sup> PAK7 (Pb-Free)	800 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NVBGS1D2N08H

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	80			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250\ \mu\text{A}$ , ref to $25^\circ\text{C}$		56		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = 80\text{ V}$	$T_J = 25^\circ\text{C}$		10	$\mu\text{A}$
			$T_J = 125^\circ\text{C}$		250	$\mu\text{A}$
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA

### ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 650\ \mu\text{A}$	2.0	2.9	4.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	$I_D = 650\ \mu\text{A}$ , ref to $25^\circ\text{C}$		-7.5		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 50\text{ A}$		1.1	1.34	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = 5\text{ V}, I_D = 50\text{ A}$		213		S
Gate-Resistance	$R_G$			0.5		$\Omega$

### CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}, f = 1\text{ MHz}$		10830		pF
Output Capacitance	$C_{OSS}$			1605		
Reverse Transfer Capacitance	$C_{RSS}$			45		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 40\text{ V}; I_D = 50\text{ A}$		160		nC
Threshold Gate Charge	$Q_{G(TH)}$			28		
Gate-to-Source Charge	$Q_{GS}$			43		
Gate-to-Drain Charge	$Q_{GD}$			33		
Plateau Voltage	$V_{GP}$			4.3		

### SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 64\text{ V}, I_D = 50\text{ A}, R_G = 6\ \Omega$		40		ns
Rise Time	$t_r$			34		
Turn-Off Delay Time	$t_{d(OFF)}$			134		
Fall Time	$t_f$			45		

### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0\text{ V}, I_S = 50\text{ A}$	$T_J = 25^\circ\text{C}$		0.8	1.3	V
			$T_J = 125^\circ\text{C}$		0.65		
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0\text{ V}, di_S/dt = 100\text{ A}/\mu\text{s}, I_S = 50\text{ A}$			78		ns
Reverse Recovery Charge	$Q_{RR}$				122		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .

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## TYPICAL CHARACTERISTICS

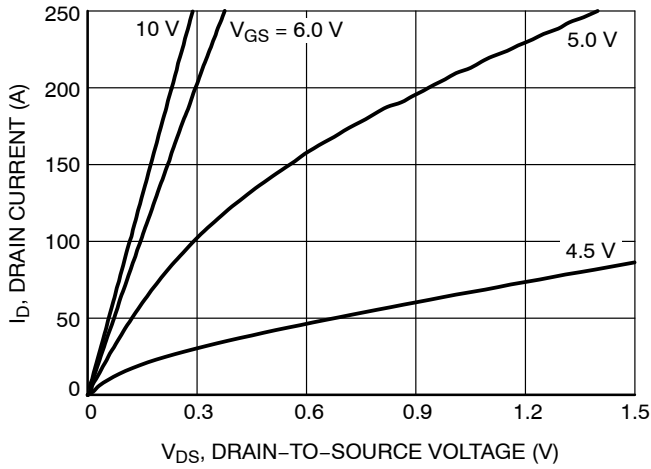


Figure 1. On-Region Characteristics

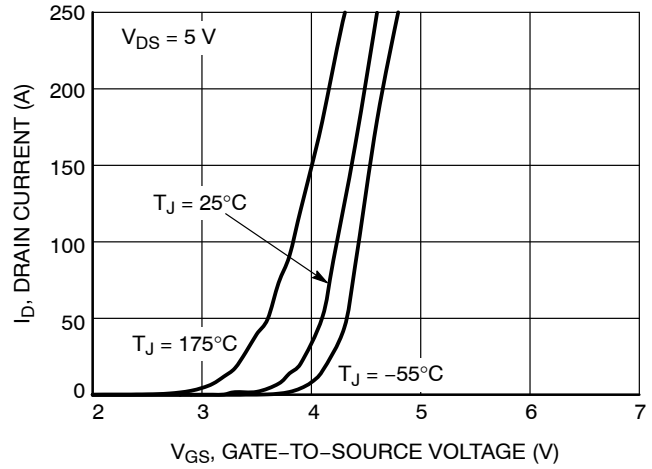


Figure 2. Transfer Characteristics

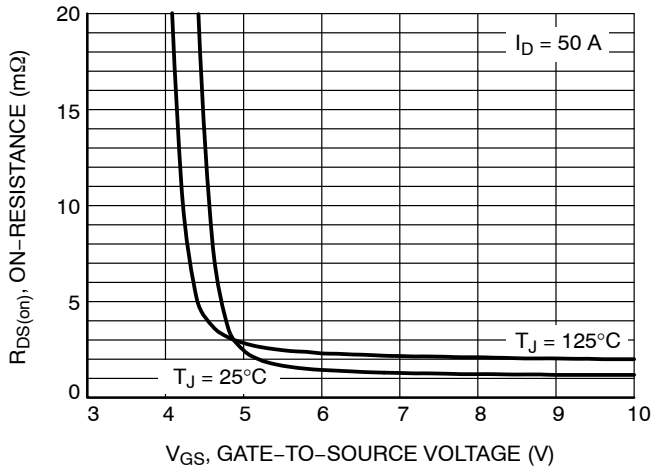


Figure 3. On-Resistance vs. Gate-to-Source Voltage

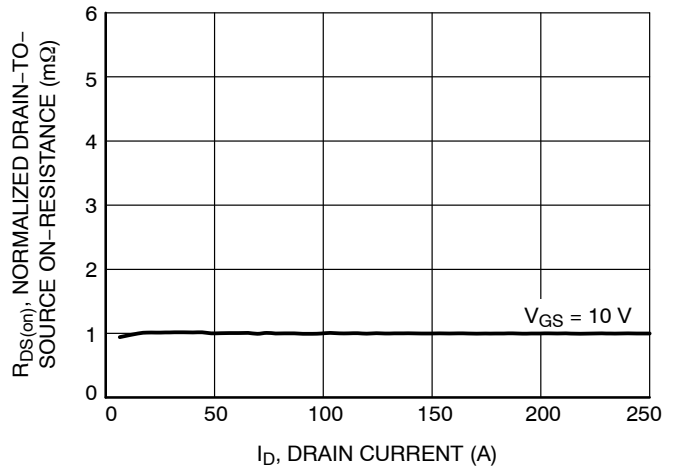


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

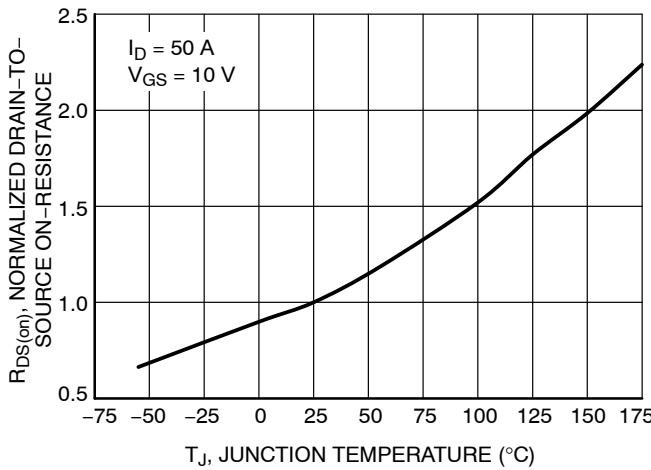


Figure 5. On-Resistance Variation with Temperature

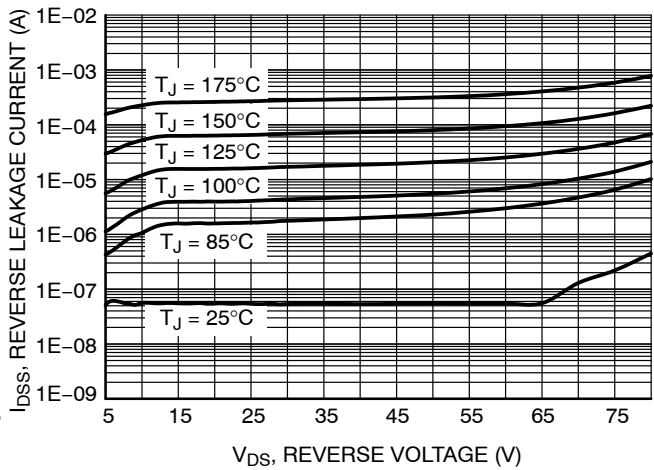


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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## TYPICAL CHARACTERISTICS

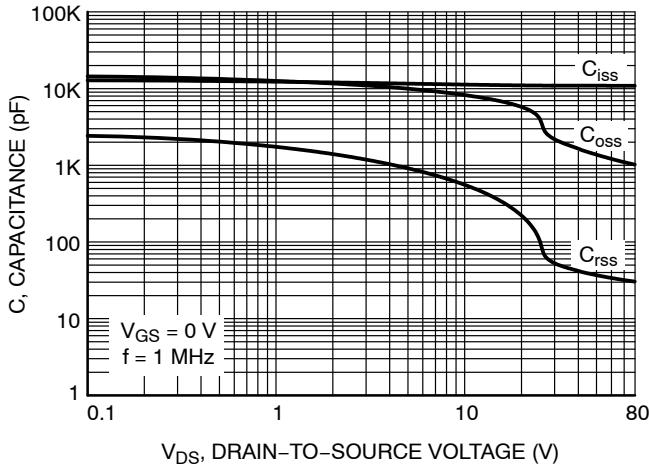


Figure 7. Capacitance Variation

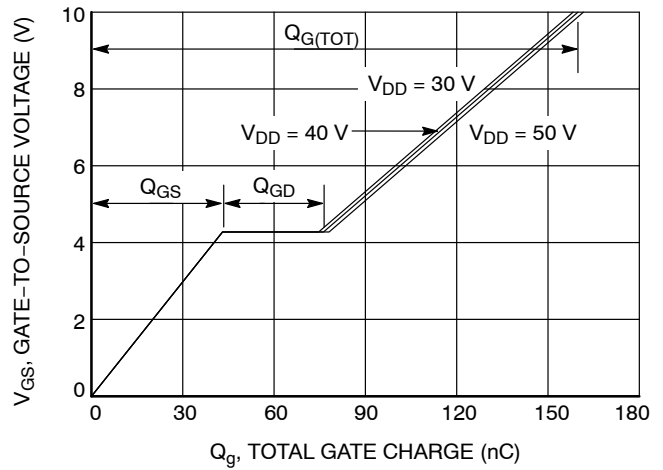


Figure 8. Gate-to-Source vs. Total Charge

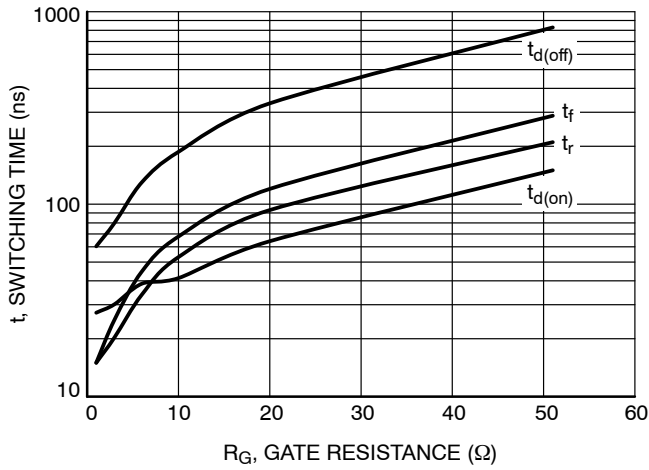


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

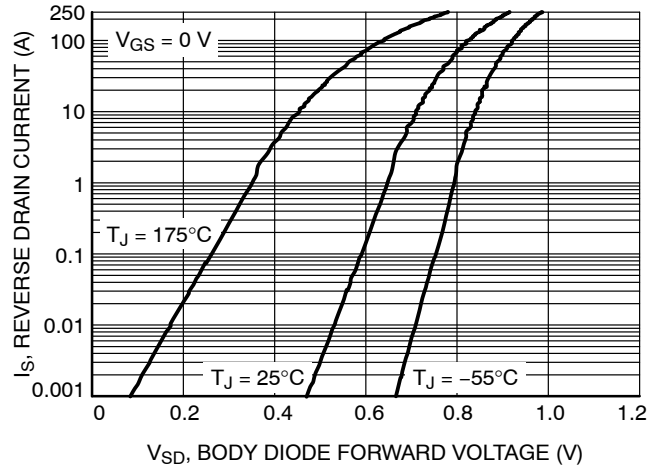


Figure 10. Diode Forward Voltage vs. Current

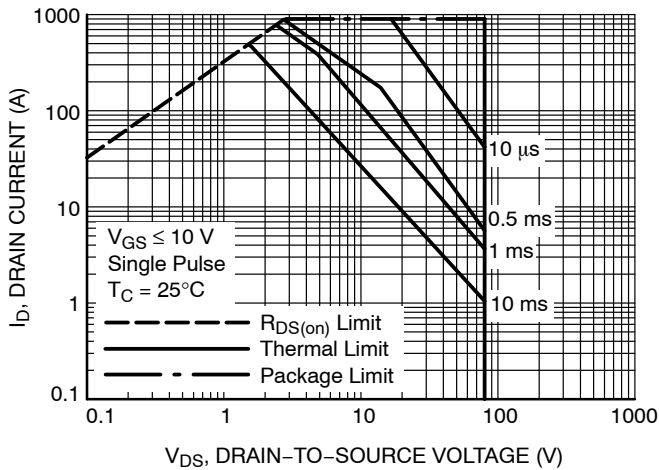


Figure 11. Maximum Rated Forward Biased Safe Operating Area

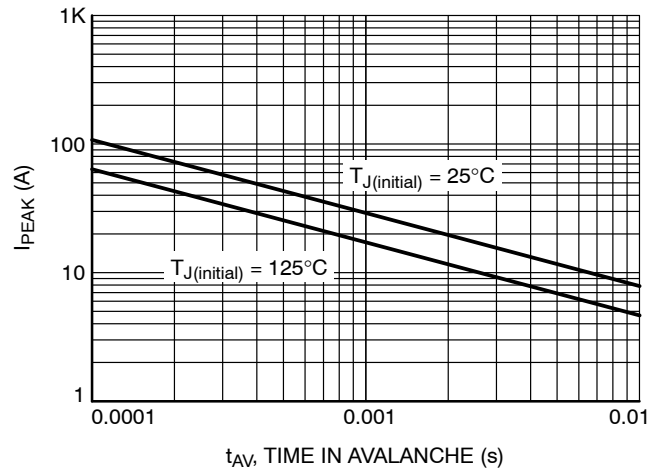


Figure 12. Maximum Drain Current vs. Time in Avalanche

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## TYPICAL CHARACTERISTICS

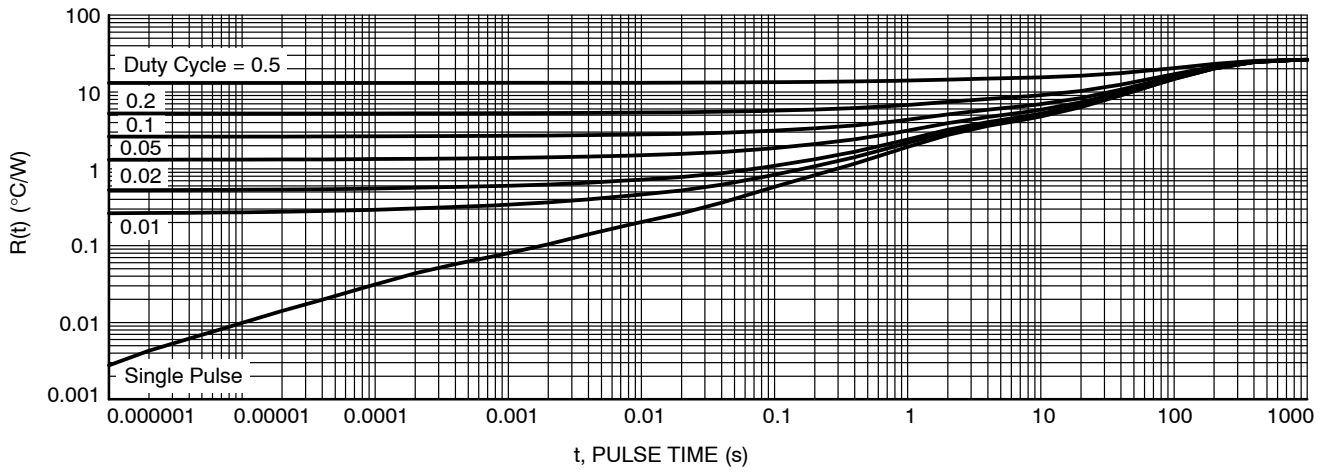
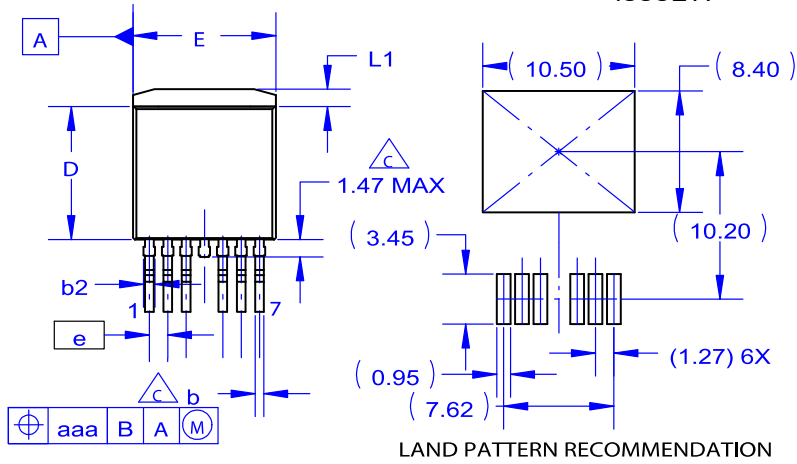


Figure 13. Transient Thermal Impedance

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## PACKAGE DIMENSIONS

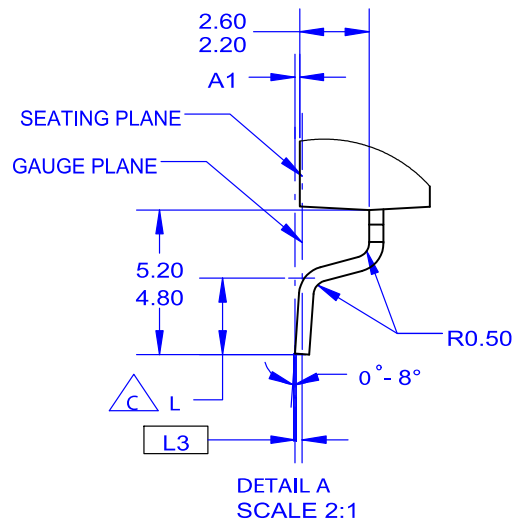
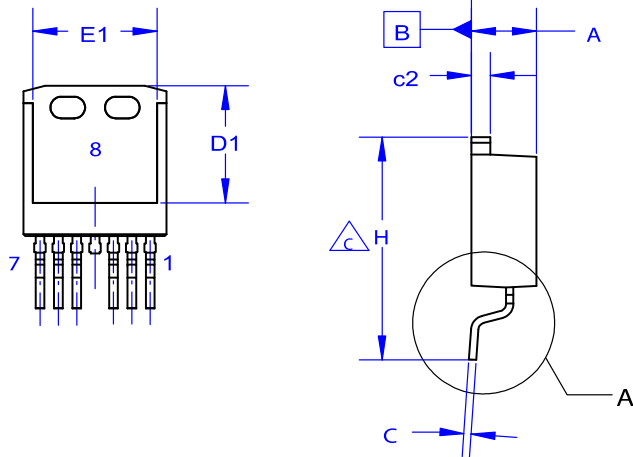
**D2PAK7 (TO-263-7LD) 15.4x9.9x4.5**  
 CASE 221BP  
 ISSUE A




**NOTES:**

- A. PACKAGE CONFORMS TO JEDEC TO-263 VARIATION CB EXCEPT WHERE NOTED.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- △ OUT OF JEDEC STANDARD VALUE.
- D. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.
- E. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- F. LAND PATTERN RECOMMENDATION PER IPC-TO127P1524X465-8N.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.30	4.50	4.70
A1	0.00	0.10	0.20
b2	0.60	0.70	0.80
b	0.50	0.60	0.70
c	0.40	0.50	0.60
c2	1.20	1.30	1.40
D	9.00	9.20	9.40
D1	7.30	7.80	8.20
E	9.70	9.90	10.20
E1	7.15	8.05	8.55
e	~	1.27	~
H	15.10	15.40	15.70
L	2.44	2.64	2.84
L1	1.00	1.20	1.40
L3	~	0.25	~
aaa	~	~	0.25



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